

TEM Simulations of Tilted Atomically Thin Hexagonal Boron Nitride Sheets

M.L. Odlyzko and K.A. Mkhoyan

Department of Chemical Engineering and Materials Science, University of Minnesota, Twin Cities, Minneapolis, MN 55455

Atomically thin hexagonal boron nitride (h-BN), comprised of covalently bonded honeycomb sheets bound by weakly ionic interplanar attractions, has garnered significant interest as a structural analog of graphene with distinctive chemical and electronic properties [1]. TEM characterization is an ideal candidate for atomic-scale analysis of the structure and bonding of few-layer h-BN, and the imaging of h-BN flakes with regions as thin as a single layer has been demonstrated by both bright-field conventional TEM (BF-CTEM) [2,3] and annular-dark-field scanning TEM (ADF-STEM) [4].

Although the BF-CTEM studies have shown that regions of different thickness can be distinguished by relative phase measurements extracted from through-focal-series data, it is useful to study alternative means to determine the thickness of few-layer h-BN. In particular, it is desirable to determine thickness from unprocessed data. To this end, we have employed TEM simulations to demonstrate that sheets of thickness 1 to 4 layers can be clearly distinguished by the evolution of ADF-STEM images and selected-area diffraction patterns (SADPs) as the samples are tilted away from the [0001] zone axis orientation.

Simulations were performed using the TEMSIM multislice package [5]. Images and diffraction patterns were simulated for a 100 keV aberration-corrected microscope. Sheets 1–4 layers thick were analyzed at tilts 0, 20, 50, 100, 200, and 500 mrad relative to [0001] about the $\langle 10\bar{1}0 \rangle$ ("x-tilt") and $\langle 11\bar{2}0 \rangle$ ("y-tilt") crystallographic axes. Thermal diffuse scattering was included by averaging many phonon configurations at 300 K.

Similar to the standard study on few-layer graphite [6], parallel-beam diffraction simulations show that SADPs from single-layer h-BN maintain full hexagonal symmetry irrespective of tilt whereas thicker sheets have spots fade and disappear. Figure 1 compares tilt effects on parallel-beam diffraction for x-tilts of 1-layer and 2-layer h-BN. Similar patterns are observed for y-tilts.

ADF-STEM images were simulated for a high-angle annular detector with acceptance angle range 54–340 mrad. Both x-tilt (figure 2) and y-tilt (figure 3) series show that 1-layer h-BN only slightly distorts the hexagonal symmetry of the image, while regions 2–4 layers thick exhibit distinctive smearing patterns as the result of the multi-atom (0001) columns being tilted off of the optic axis. This suggests that ADF-STEM imaging also can be used to distinguish 1-layer h-BN from multilayer samples [7].

References

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[7] This research was supported by University of Minnesota and NSF grant DMR-1006706

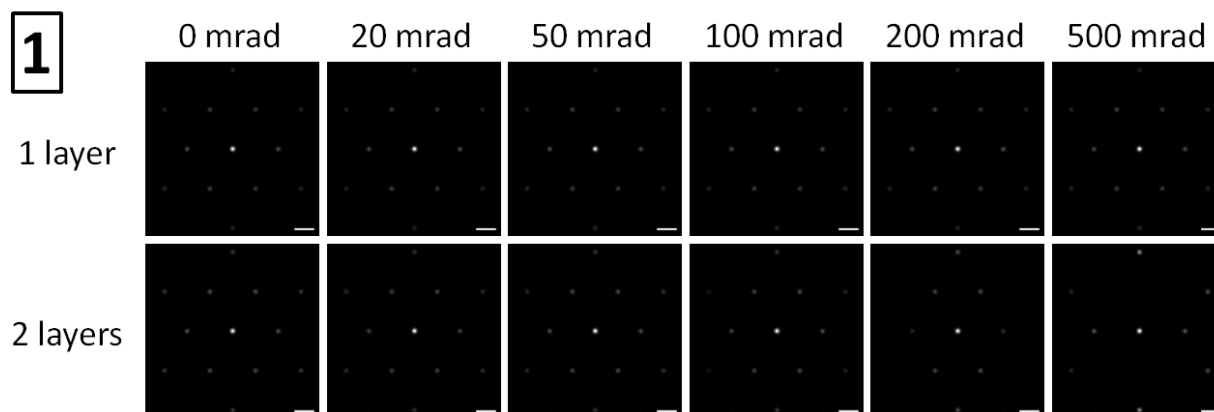


FIG. 1. SADP tilt series about $\langle 10\bar{1}0 \rangle$ crystallographic axis for few-layer h-BN. Scale bars have length 2 nm^{-1} .

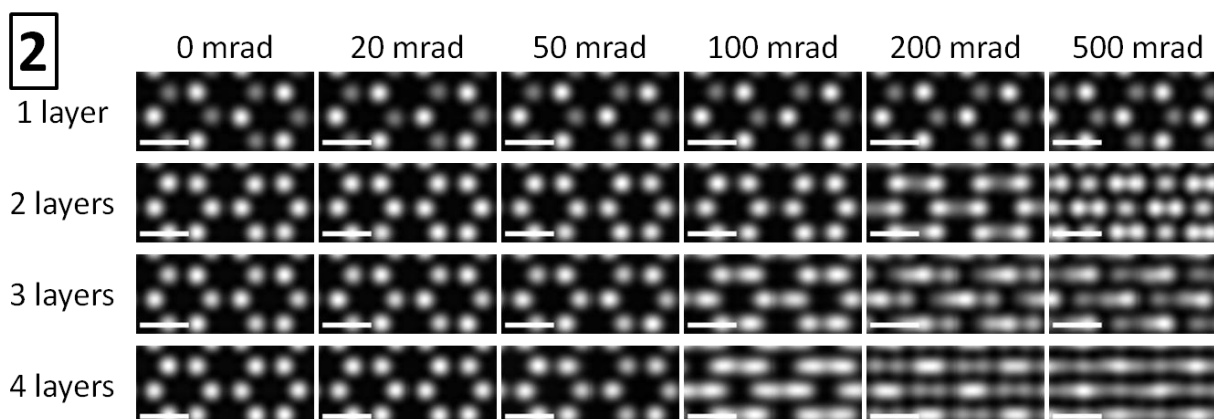


FIG. 2. ADF-STEM image tilt series about $\langle 10\bar{1}0 \rangle$ crystallographic axis for few-layer h-BN. Scale bars have length 2 \AA .

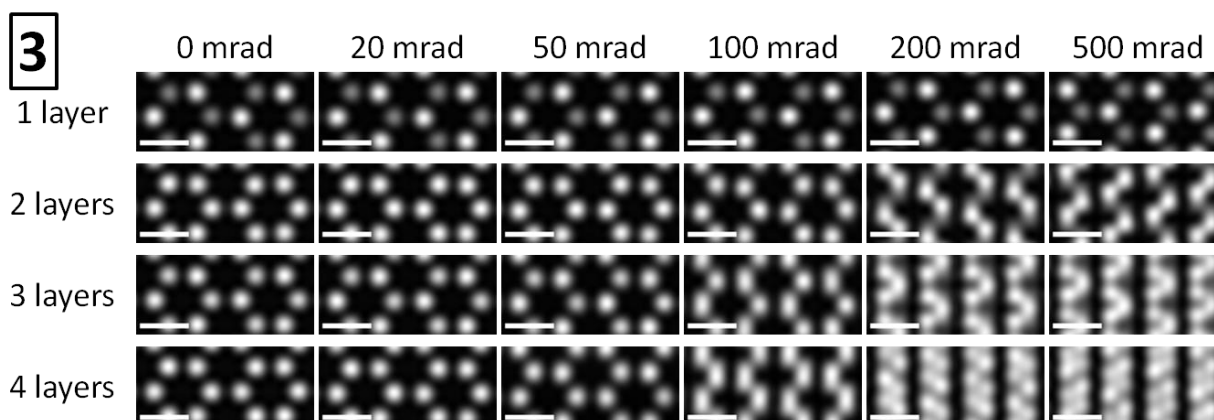


FIG. 3. ADF-STEM image tilt series about $\langle 11\bar{2}0 \rangle$ crystallographic axis for few-layer h-BN. Scale bars have length 2 \AA .